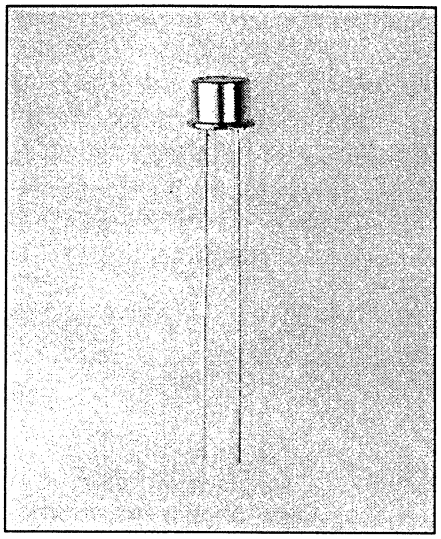
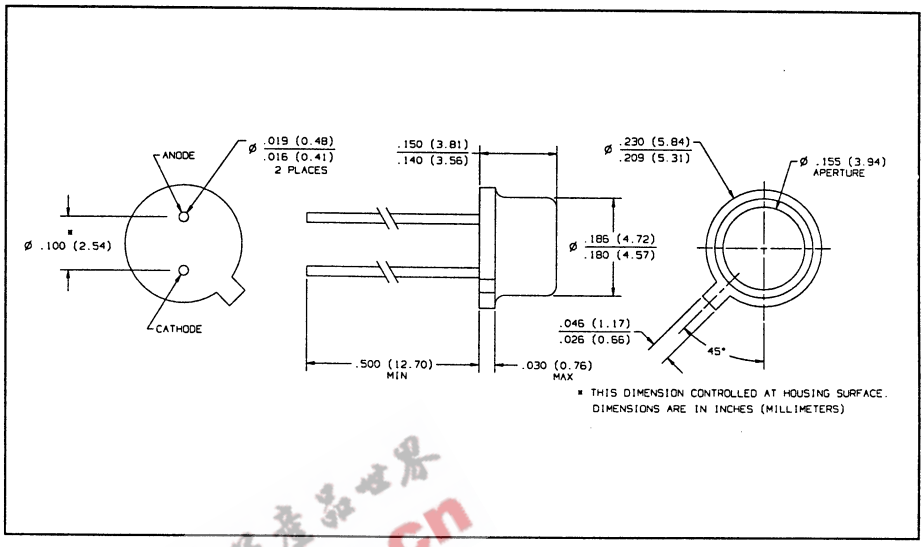
GaAs Hermetic Infrared Emitting Diodes
Types OP130W, OP131W, OP132W, OP133W





Features

- Wide irradiance pattern
- Enhanced temperature range
- Mechanically and spectrally matched to the OP800WSL and OP830WSL series devices
- Variety of power ranges
- TO-46 hermetically sealed package

Description

The OP130W series devices are 935nm gallium arsenide infrared emitting diodes mounted in hermetically sealed packages. The broad irradiance pattern provides relatively even illumination over a large area.

Replaces

K6200 series

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Reverse Voltage	2.0 V
Continuous Forward Current	100 mA
Peak Forward Current (2 µs pulse width, 0.1% duty cycle)	10.0 A
Storage Temperature Range	-65° C to +150° C
Operating Temperature Range	-65° C to +125° C
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron]	260° C(1)
Power Dissipation	200 mW(2)

Notes:
(1) RMA flux is recommended. Duration can be extended to 10 seconds max. when flow soldering.
(2) Derate linearly 2.0 mW/° C above 25° C.
(3) Measurement made with 100 µs pulse measured at the trailing edge of the pulse with a duty cycle of 0.1% and an I_F = 100 mA.

Typical Performance Curves

Coupling Characteristics of OP130W and OP800W